



Patent  
Attorney's Docket No. 026350-028

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**In re Patent Application of**

Toshiro HIRAMOTO et al

Application No.: 09/389,321

Filed: September 3, 1999

For: MOS TRANSISTOR WITH A  
CONTROLLED THRESHOLD  
VOLTAGE

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Group Art Unit: 2836  
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Examiner: T. Dickey  
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**AMENDMENT UNDER 37 C.F.R. §1.111**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Date: August 7, 2001

Sir:

This Amendment responds to the Office Action dated February 9, 2001 (Paper No.

6). Concurrently filed with this Amendment is a Petition for Extension of Time for a Three Month Period and a copy of the priority document. Please amend the above-noted application as follows:

### IN THE ABSTRACT:

Please replace the abstract as follows:

A MOS transistor with a controlled threshold voltage includes a SOI which includes a substrate composed of a semi-conducting material, a single crystal layer composed of a semi-conducting material and an insulating layer interposed between the substrate and the single crystal layer. The single crystal layer is formed therein with a source region, a drain region and a surrounded region surrounded by the source region and the drain